AMENDMENTS TO THE SPECIFICATION

Please replace the translated PCT title with the following rewritten title:

PROCESS FOR PRODUCING LIGHT ABSORBING LAYER FOR CHALCOPYRITE TYPE ~~BASE LIGHT ABSORBING LAYER FOR~~ THIN-FILM SOLAR CELL

Please replace paragraph number **[0022]** with the following rewritten paragraph:

[0022]

According to the present invention, the second ~~elenization~~ selenization step may include an evacuating step of interrupting the supply of hydrogen selenide gas and evacuating the interior of the airtight space.

Please replace paragraph number **[0036]** with the following rewritten paragraph:

[0036]

Figure 4 is a schematic diagram showing a heat treatment chamber 40 for selenizing the precursor according to the present invention and Figure 4 corresponds to the selenization of the precursor for the light absorbing layer shown in Figure 2(e). The heat treatment chamber 40 is heated by heaters 41 disposed on both sides thereof. After the substrates 1c are accommodated in batches into a quartz ~~port~~ boat (cabinet) 42 by a transfer robot, the quartz boat 42 having the two or more substrates 1c accommodated upright on its bottom is inserted from the bottom of the heat treatment chamber 40 and is placed into the heat treatment chamber 40. Further, a quartz receptor 43 is provided for keeping the substrates 1c upright on

the boat 42. A rotary drive shaft 44 connected to an external driving mechanism is joined via a joint 45 to the quartz boat 42 provided with the receptor 43. While keeping the substrates 1c accommodated upright, the boat 42 can be rotated by driving the rotary shaft 44.

Please replace paragraph number **[0045]** with the following rewritten paragraph:

[0045]

Example 2

As in Example 1, the glass substrates 1c on which the In metal layer and the Cu-Ga alloy layer are superimposed are accommodated in the heat treatment chamber 40. Then, selenization is performed according to a temperature profile shown in Figure 6. The temperature profile of this example is different from that of Figure 5 in that H_2Se gas is supplied with a relatively ~~a~~ low flow rate immediately after the first selenization step and the H_2Se gas is continuously supplied without interruption in the second selenization step after the temperature increases to 250° to 450°C. In Figure 6, time t_5 represents the second selenization step including heating-up time immediately after the first selenization step.